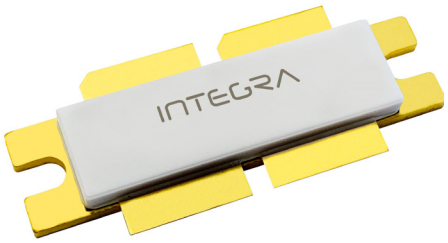
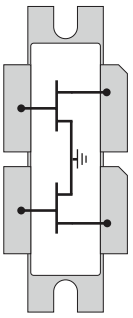
L-Band, GaN/SiC, RF Power Transistor

1.3 GHz | 3600 W | 70% Efficiency typ | 18 dB Gain typ | 100 V | 10μs Pulse Length, 1% Duty Cycle

IGN1300S3600 is a high power GaN-on-SiC RF power transistor. It operates at 1.3 GHz. Under 10μs, 1% duty cycle pulse conditions it supplies a minimum of 3600 W of peak output power, with typically 18 dB of gain and 70% efficiency. It operates from a 100 V supply voltage. For optimal thermal efficiency, the transistor is housed in a metal-based package with an epoxy-sealed ceramic lid.





FEATURES

- GaN on SiC HEMT Technology
- Output Power >3600 W
- Pre-matched Input Impedance
- High Efficiency - 70% typical
- RoHS and REACH Compliant

APPLICATIONS

- ISM Systems

Table 1. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	400	V	25 °C
DC Gate-Source Voltage	V_{GS}	-8 to +1	V	25 °C
DC Drain Current	I_D	78	A	25 °C
DC Gate Current	I_G	78	mA	25 °C
RF Input Power	$P_{RF,IN}$	85	W	25 °C
Operating Channel Temperature	T_J	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +1100	°C	
Soldering Temperature	T_{SOLDER}	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 2.DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_P	-5			V	V_{DS} = 100V, I_{DS} = 1mA
Quiescent Gate Voltage	V_Q		-2.8		V	V_{DS} = 100V, I_{DS} = 75mA per side

Table 3. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gain	G		18		dB	P_{OUT} =3600W f = 1300 MHz V_{DS} = 100V, I_{DS} = 75mA per side 10µs, 4%
Drain Efficiency During the Pulse	η		70		%	
Input Return Loss	IRL		12		dB	
Pulse Droop	D		-0.2		dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	5:1				

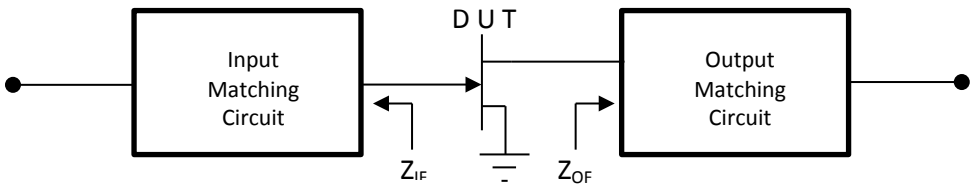
Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Typ	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	R_{TH}	0.06	°C/W	P_{DISS} = 1400W 10µs Pulse length, 1% Duty Cycle V_{DS} = 100V

Table 5. Test Fixture One Side to Ground Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (MHz)	Z_{IF}	Z_{OF} Fundamental	Z_{OF} Second Harmonic	Units	Test Conditions
1300	0.95 - j 1.06	1.92 - j 2.24	0.53 + j 3.06	Ω	P_{OUT} = 3600W 10µs Pulse length, 1% Duty Cycle V_{DS} = 100V, I_{DS} = 75mA per side



TYPICAL PERFORMANCE

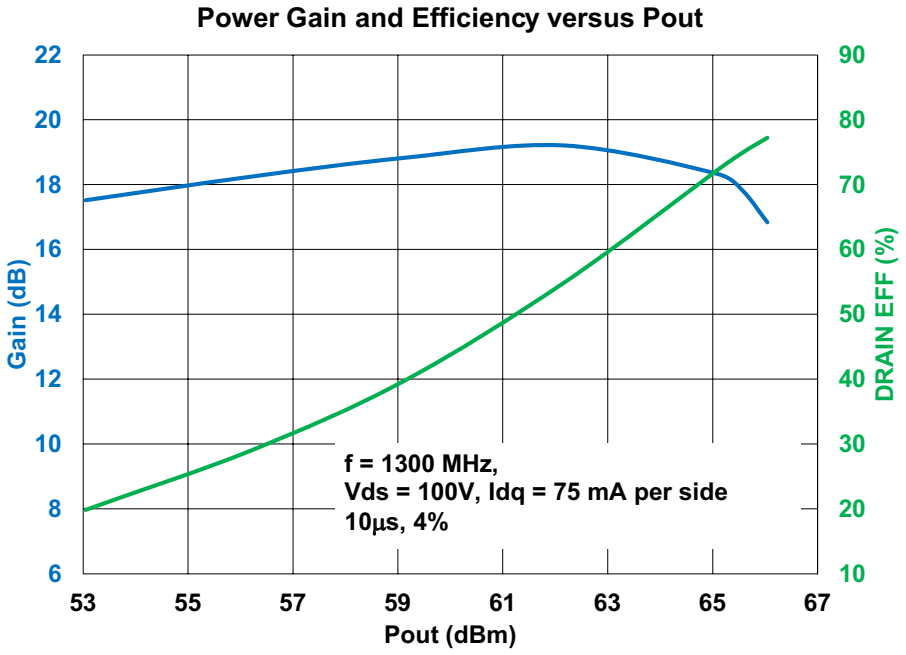


Figure1

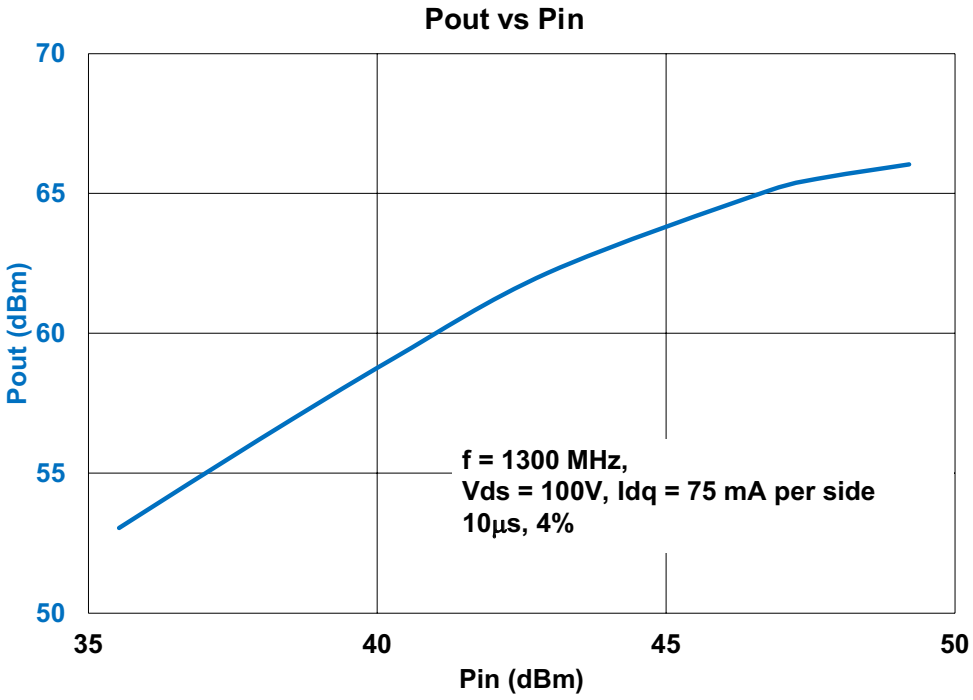
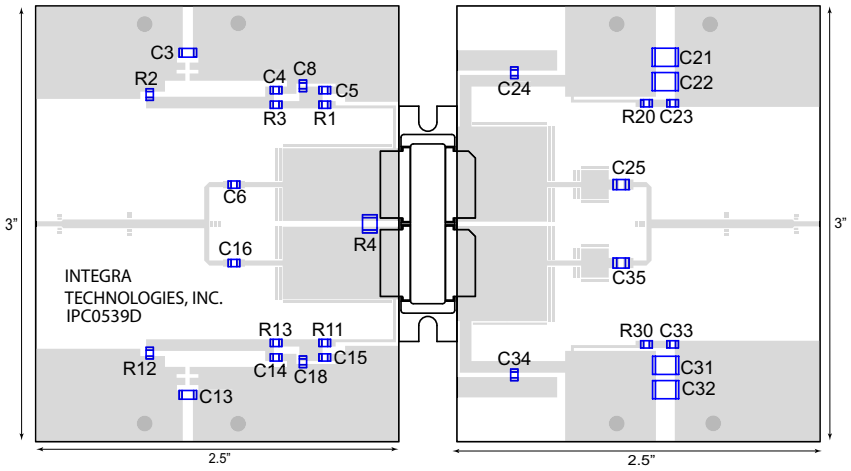


Figure 2

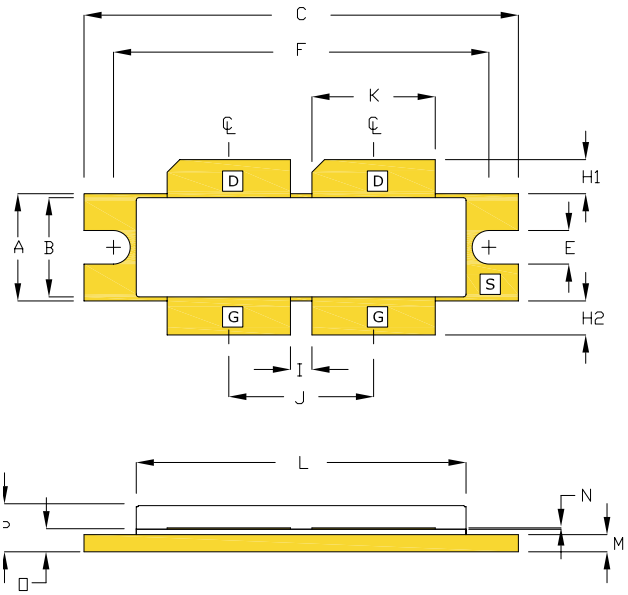
TEST FIXTURE



Bill of Materials for IGN1300S3600 Test Fixture

Designator	Description	Part Number
C3, C13	CAP 1μF, 1206, 100V, X7R	12061C105K4T2A
C4, C14, C23, C33	CAP 0.068μF, 250V, 0805, X7R	C0805C683KARAC#A
C5, C6, C15, C16, C24, C34	CAP 33pF, 0805	ATC600F330
C8, C18	CAP 1000pF, 100V, 0805	08051A102J4T2A
C25, C35	CAP 150pF, 1111	800B151JT300XT
C22, C23, C31, C32	CAP 2.2μF, 2220, 250V, X7R	C5750X7T2E225K250KA
R1, R11, R20, R30	RES 15 OHM, 0805	CRCW080515R0JNEA
R2, R12	RES 100 OHM, 0805	CRCW0805100RFKTA
R3, R13	RES 0 OHM, 0805	CRCW08050000ZSTA
R4	RES 5.1 OHM, 1210	CRCW12105R10JNEA
PC Board Type	ROGERS RO3006, 25mil, 2/2oz. Copper	

PACKAGE PL124A1



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.395	0.405	10.03	10.29
B	0.366	0.374	9.29	9.49
C	1.615	1.625	41.02	41.27
E	0.120	0.130	3.05	3.30
F	1.395	1.405	35.43	35.69
H1	0.120	0.130	3.05	3.30
H2	0.120	0.130	3.05	3.30
I	0.075	0.085	1.90	2.16
J	0.535	0.545	13.59	13.84
K	0.455	0.465	11.55	11.81
L	1.218	1.242	30.93	31.54
M	0.059	0.069	1.499	1.752
N	0.004	0.007	0.10	0.18
□	0.079	0.089	2.00	2.26
P	0.165	0.188	4.19	4.77

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivty Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DATA SHEET STATUS
Advanced Specification - This data sheet contains Advanced specifications.
Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.
Final Specification - This data sheet contains final product specifications.
MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865